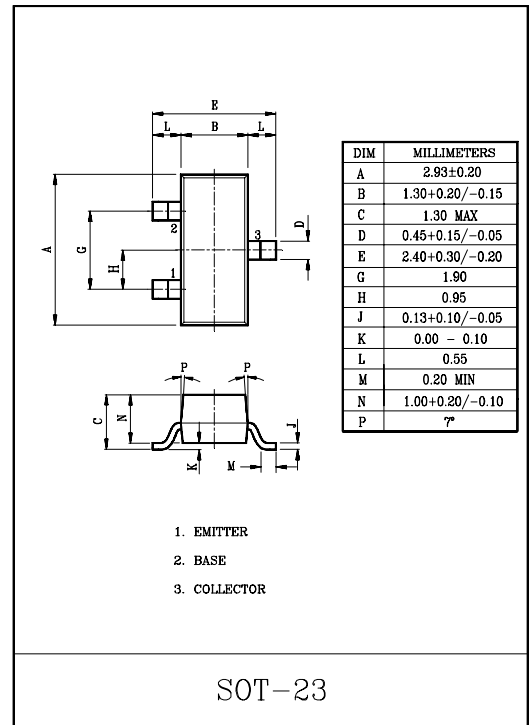


HIGH FREQUENCY APPLICATION.
VHF BAND AMPLIFIER APPLICATION.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	BFS20	4	V
	BF599	5	
Collector Current	I _C	25	mA
Emitter Current	I _E	-25	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-65~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	BFS20	V _{(BR)CBO} I _C =10μA, I _E =0	40	-	-	V
Collector-Emitter Breakdown Voltage		V _{(BR)CEO} I _C =2mA, I _B =0	25	-	-	V
Emitter-Base Breakdown Voltage		V _{(BR)EBO} I _E =10μA, I _C =0	4.0	-	-	V
Collector Cut-off Current	BFS20	I _{CBO} V _{CB} =20V, I _E =0	-	-	100	nA
			V _{CB} =20V, I _E =0, Ta=150°C	-	-	10
	BF599	V _{CB} =40V, I _E =0	-	-	100	nA
DC Current Gain		h _{FE} V _{CE} =10V, I _C =7mA	40	-	-	-
Base-Emitter Voltage	BFS20	V _{BE(ON)} V _{CE} =10V, I _C =7mA	-	750	900	mV
	BF599		-	750	-	
Transition Frequency	BFS20	f _T V _{CE} =10V, I _C =7mA, f=100MHz	275	550	-	MHz
	BF599		-	550	-	
Collector Output Capacitance		C _{ob} V _{CB} =10V, f=1MHz, I _E =0	-	0.35	-	pF

MARK SPEC

TYPE	MARK
BFS20	G1
BF599	G2

Marking

